

## INCHANGE SEMICONDUCTOR

## isc P-Channel MOSFET Transistor

## AOD409

### • FEATURES

- With TO-252( DPAK ) packaging
- High speed switching
- · Low gate input resistance
- Standard level gate drive
- · Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATIONS

- Power supply
- Switching applications

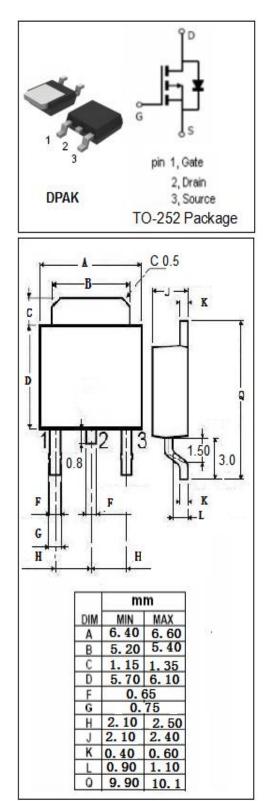
| SYMBOL           | PARAMETER                                  | VALUE      | UNIT |  |  |  |  |
|------------------|--|------------|------|--|--|--|--|
| V <sub>DSS</sub> | Drain-Source Voltage                       | -60        | V    |  |  |  |  |
| V <sub>GSS</sub> | Gate-Source Voltage                        | ±20        | V    |  |  |  |  |
| ID               | Drain Current-Continuous@Tc=25℃<br>Tc=100℃ | -26<br>-18 | А    |  |  |  |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed                | -60        | А    |  |  |  |  |
| PD               | Total Dissipation                          | 60         | W    |  |  |  |  |
| Tj               | Operating Junction Temperature             | 175        | °C   |  |  |  |  |
| T <sub>stg</sub> | Storage Temperature                        | -55~175    | °C   |  |  |  |  |

## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

#### • THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                             |     | UNIT         |  |
|-----------|---------------------------------------|-----|--------------|--|
| Rth(ch-c) | Channel-to-case thermal resistance    | 2.5 | °C <b>/W</b> |  |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 50  | °C/W         |  |

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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL               | PARAMETER                      | CONDITIONS  | MIN  | ТҮР | MAX      | UNIT |
|----------------------|--------------------------------|---|------|-----|----------|------|
| BV <sub>DSS</sub>    | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = -0.25mA                 | -60  |     |          | V    |
| V <sub>GS</sub> (th) | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =-0.25mA    | -1.2 |     | -2.4     | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance     | V <sub>GS</sub> = -10V; I <sub>D</sub> =-20A                  |      | 32  | 40       | mΩ   |
| I <sub>GSS</sub>     | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V                    |      |     | ±0.1     | μA   |
| I <sub>DSS</sub>     | Drain-Source Leakage Current   | V <sub>DS</sub> = -48V; V <sub>GS</sub> = 0V;Tj=25℃<br>Tj=55℃ |      |     | -1<br>-5 | μA   |
| V <sub>SDF</sub>     | Diode forward voltage          | I <sub>SD</sub> =-1A, V <sub>GS</sub> = 0 V                   |      |     | -1       | V    |

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